NTR2101P

Small Signal MOSFET

−8.0 V, −3.7 A, Single P−Channel, SOT−23

Features

- Leading Trench Technology for Low $R_{DS(on)}$
- −1.8 V Rated for Low Voltage Gate Drive
- SOT−23 Surface Mount for Small Footprint (3 x 3 mm)
- This is a Pb−Free Device

Applications

- High Side Load Switch
- DC−DC Conversion
- Cell Phone, Notebook, PDAs, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−8.0	V
Gate−to−Source Voltage			V_{GS}	±8.0	V
Continuous Drain Current (Note 1)	t≤10 s	T_A = 25°C	I_D	−3.7	A
		T_A = 70°C		−3.0	
Power Dissipation (Note 1)	t≤10 s		P_D	0.96	W
Pulsed Drain Current	tp = 10 μs		I_{DM}	−11	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−1.2	A
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient – Steady State	$R_{\theta JA}$	160	°C/W
Junction−to−Ambient − t≤10 s	$R_{\theta JA}$	130	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

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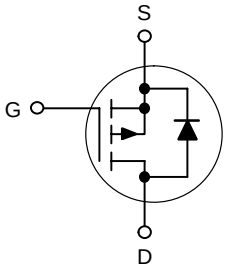
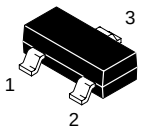
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max
−8.0 V	39 mΩ @ −4.5 V	−3.7 A
	52 mΩ @ −2.5 V	
	79 mΩ @ −1.8 V	

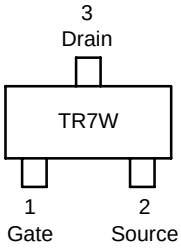
P−Channel MOSFET



MARKING DIAGRAM & PIN ASSIGNMENT



SOT−23
CASE 318
STYLE 21



TR7 = Device Code
W = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
NTR2101PT1	SOT−23	3000/Tape & Reel
NTR2101PT1G	SOT−23 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−8.0			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				10		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −6.4 V	T_J = 25°C			−1.0	μA
			T_J = 125°C			−100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8.0 V				±100	nA
ON CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−0.40			V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				0.0027		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = −4.5 V, I_D = −3.5 A			39	52	mΩ
		V_{GS} = −2.5 V, I_D = −3.0 A			52	72	
		V_{GS} = −1.8 V, I_D = −2.0 A			79	120	
Forward Transconductance	g_{FS}	V_{GS} = −5.0 V, I_D = −3.5 A			9.0		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = −4.0 V			1173		pF
Output Capacitance	C_{OSS}				289		
Reverse Transfer Capacitance	C_{RSS}				218		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −4.0 V, I_D = −3.5 A			12	15	nC
Gate−to−Source Charge	Q_{GS}				3.8		
Gate−to−Drain Charge	Q_{GD}				2.5		
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −4.0 V, I_D = −1.2 A, R_G = 6.0 Ω			7.4	15	ns
Rise Time	t_r				15.75	25	
Turn−Off Delay Time	$t_{d(OFF)}$				38	58	
Fall Time	t_f				31	51	
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −1.2 A	T_J = 25°C		−0.73	−1.2	V

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

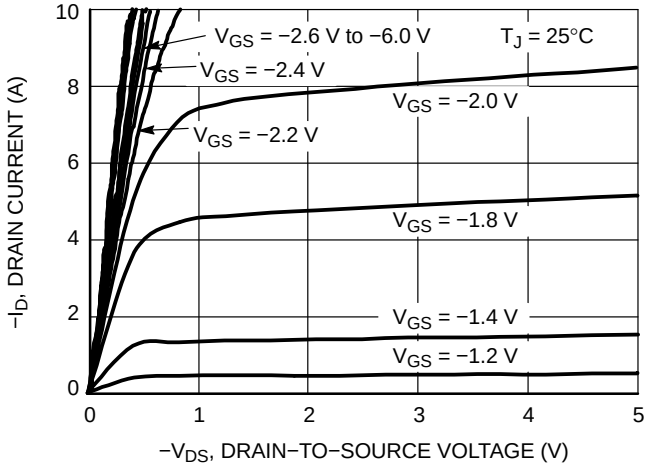


Figure 1. On−Region Characteristics

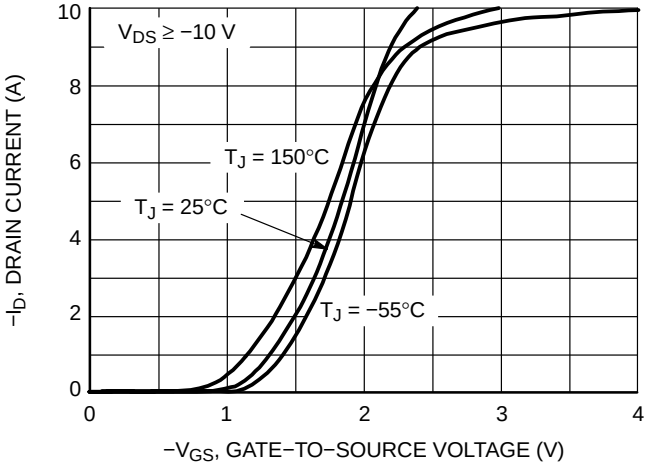


Figure 2. Transfer Characteristics

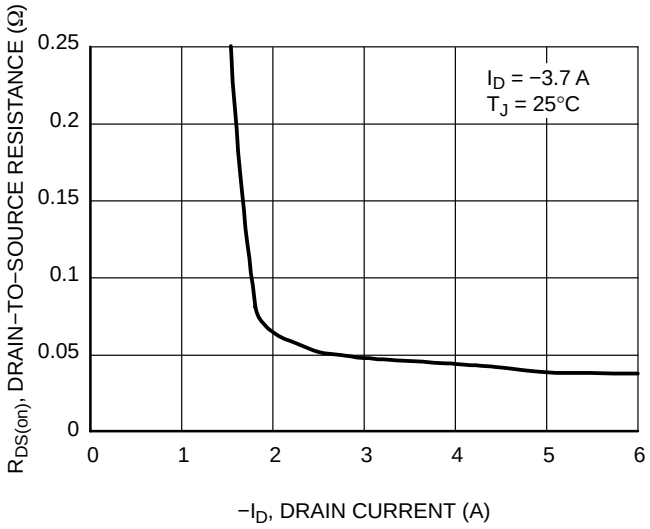


Figure 3. On−Resistance versus Gate−to−Source Voltage

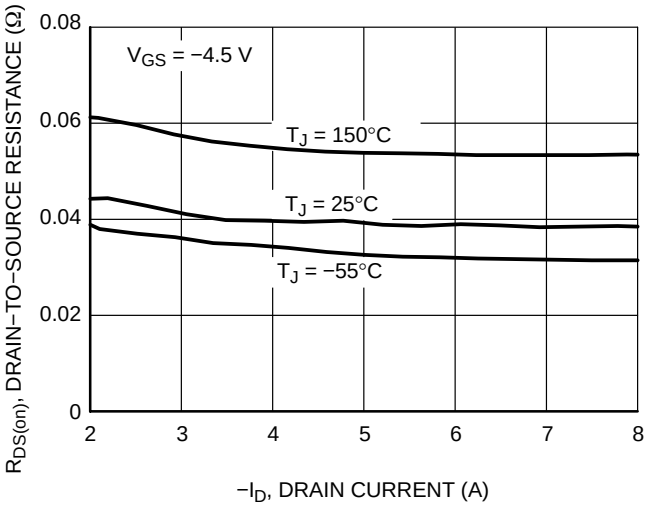


Figure 4. On−Resistance versus Drain Current and Gate Voltage

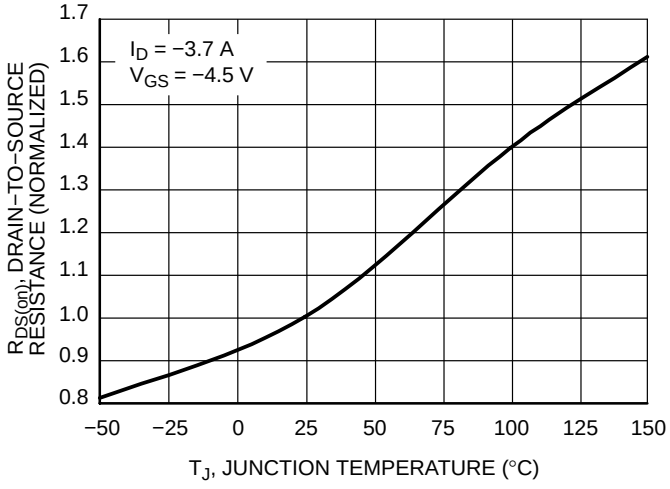


Figure 5. On−Resistance Variation with Temperature

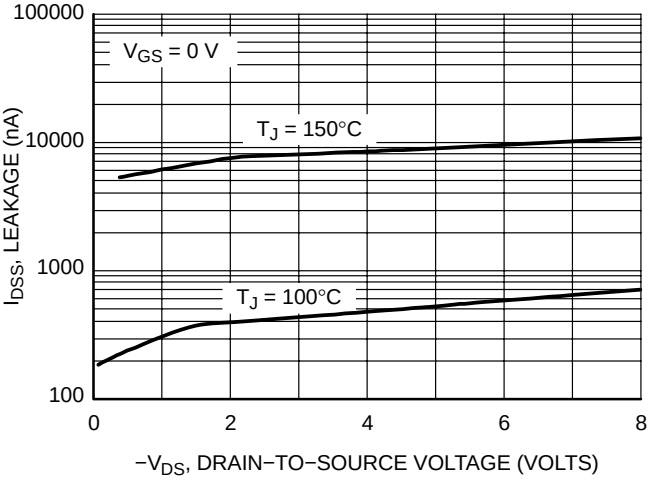


Figure 6. Drain−to−Source Leakage Current versus Voltage

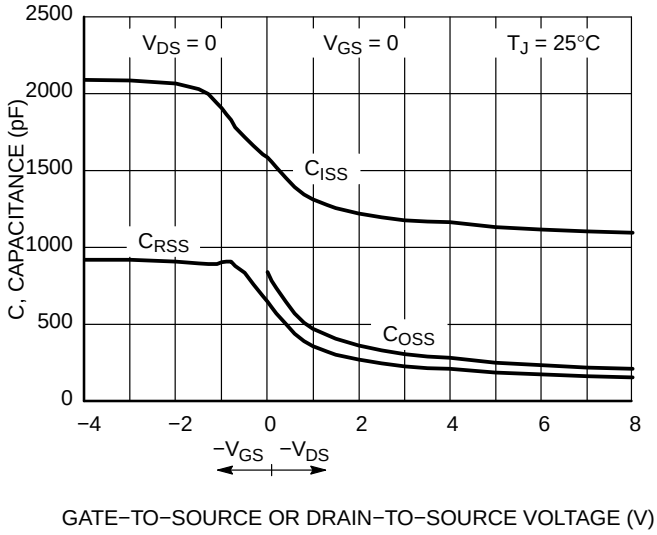


Figure 7. Capacitance Variation

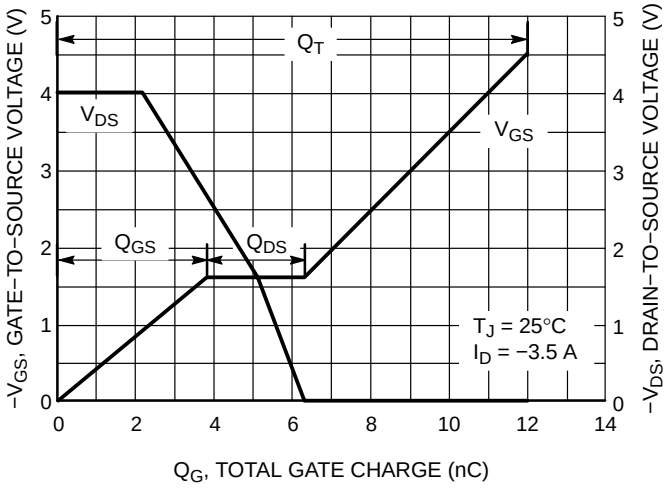


Figure 8. Gate−to−Source and Drain−to−Source Voltage versus Total Charge

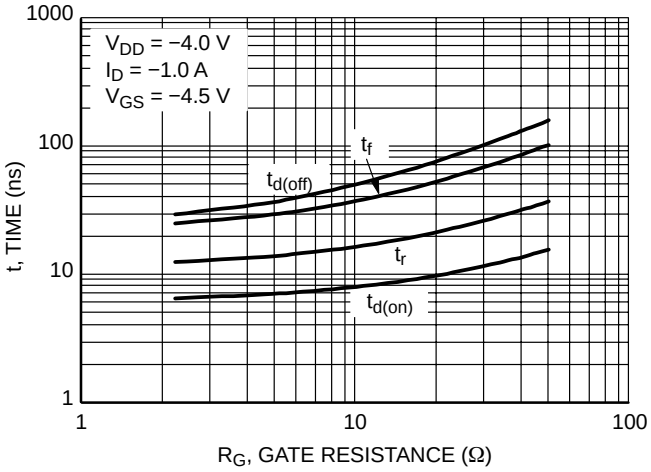


Figure 9. Resistive Switching Time Variation versus Gate Resistance

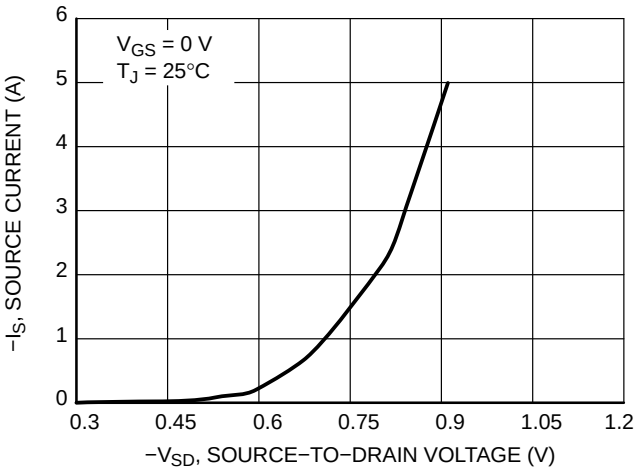
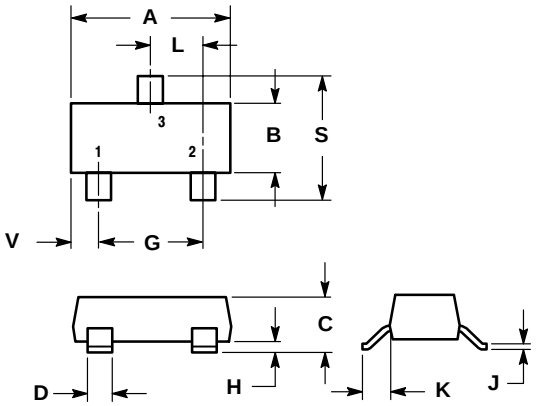


Figure 10. Diode Forward Voltage versus Current

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−09
ISSUE AH

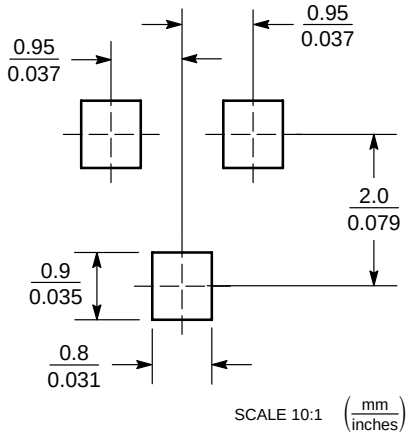


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIUMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01, −02, AND −06 OBSOLETE, NEW STANDARD 318−09.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0385	0.0498	0.99	1.26
D	0.0140	0.0200	0.36	0.50
G	0.0670	0.0826	1.70	2.10
H	0.0040	0.0098	0.10	0.25
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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